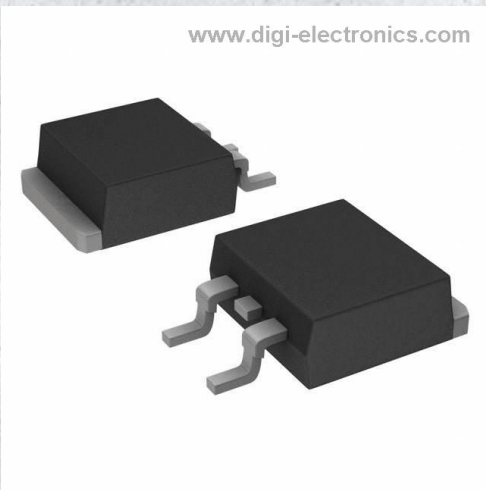
IPB107N20N3GATMA1 Datasheet



DiGi Electronics Part Number	IPB107N20N3GATMA1-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	IPB107N20N3GATMA1
Description	MOSFET N-CH 200V 88A D2PAK
Detailed Description	N-Channel 200 V 88A (Tc) 300W (Tc) Surface Mount PG-TO263-3

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
IPB107N20N3GATMA1	Infineon Technologies
Series:	Product Status:
OptiMOS™	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
200 V	88A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	10.7mOhm @ 88A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 270µA	87 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	7100 pF @ 100 V
FET Feature:	Power Dissipation (Max):
-	300W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PG-TO263-3	TO-263-3, D2PAK (2 Leads + Tab), TO-263AB
Base Product Number:	
IPB107	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

IPB107N20N3 G IPP110N20N3 G
IPI110N20N3 G

OptiMOS™3 Power-Transistor

Features

- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[1] for target application
- Halogen-free according to IEC61249-2-21
- Ideal for high-frequency switching and synchronous rectification

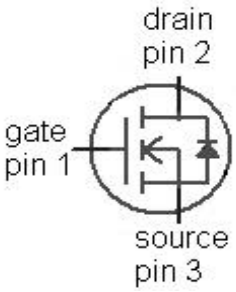
Product Summary

V_{DS}	200	V
$R_{DS(on),max\ (TO263)}$	10.7	mΩ
I_D	88	A

RoHS

Halogen-Free

Type	IPB107N20N3 G	IPP110N20N3 G	IPI110N20N3 G
			
Package	PG-TO263-3	PG-TO220-3	PG-TO262-3
Marking	107N20N	110N20N	110N20N



Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	**Symbol**	**Conditions**	**Value**	**Unit**
Continuous drain current	I_D	T_C=25 °C	88	A
		T_C=100 °C	63	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25 °C	352	
Avalanche energy, single pulse	E_{AS}	I_D=80 A, R_{GS}=25 Ω	560	mJ
Reverse diode dv/dt	dv/dt		10	kV/µs
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	T_C=25 °C	300	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

[1] J-STD20 and JESD22

[2] See figure 3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	0.5	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint	-	-	62	
		6 cm2 cooling area[3)]	-	-	40	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	200	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=270 µA	2	3	4	
Zero gate voltage drain current	I_{DSS}	V_{DS}=160 V, V_{GS}=0 V, T_j=25 °C	-	0.1	1	µA
		V_{DS}=160 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=88 A, (TO220, TO262)	-	9.9	11	mΩ
		V_{GS}=10 V, I_D=88 A, (TO263)	-	9.6	10.7	
Gate resistance	R_G		-	2.4	-	Ω
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=88 A	71	141	-	S

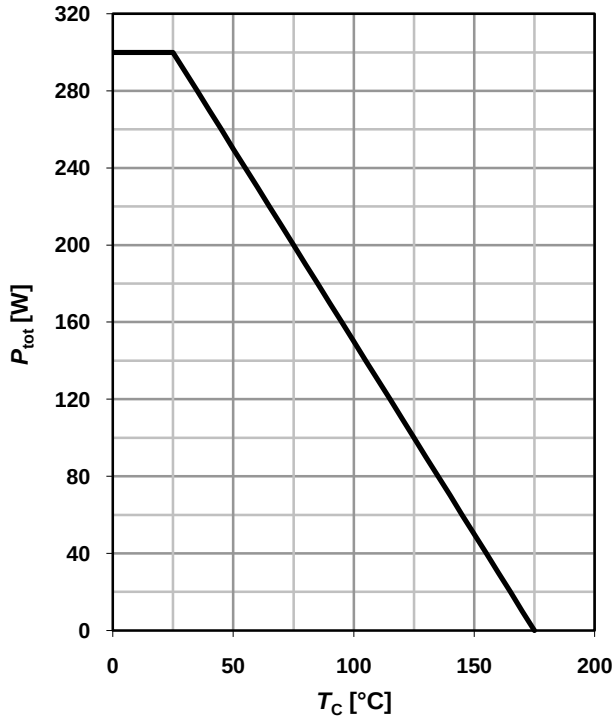
[3)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=100 V, f=1 MHz	-	5340	7100	pF
Output capacitance	C_{oss}		-	401	533	
Reverse transfer capacitance	C_{rss}		-	5	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=100 V, V_{GS}=10 V, I_D=44 A, R_G=1.6 Ω	-	18	-	ns
Rise time	t_r		-	26	-	
Turn-off delay time	$t_{d(off)}$		-	41	-	
Fall time	t_f		-	11	-	
Gate Charge Characteristics[4)]						
Gate to source charge	Q_{gs}	V_{DD}=100 V, I_D=44 A, V_{GS}=0 to 10 V	-	23	-	nC
Gate to drain charge	Q_{gd}		-	8	-	
Switching charge	Q_{sw}		-	15	-	
Gate charge total	Q_g		-	65	87	
Gate plateau voltage	$V_{plateau}$		-	4.4	-	V
Output charge	Q_{oss}	V_{DD}=100 V, V_{GS}=0 V	-	162	216	nC
Reverse Diode						
Diode continous forward current	I_S	T_C=25 °C	-	-	88	A
Diode pulse current	$I_{S,pulse}$		-	-	352	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=88 A, T_j=25 °C	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=100 V, I_F=44 A, di_F/dt=100 A/µs	-	142		ns
Reverse recovery charge	Q_{rr}		-	640	-	nC

[4)] See figure 16 for gate charge parameter definition

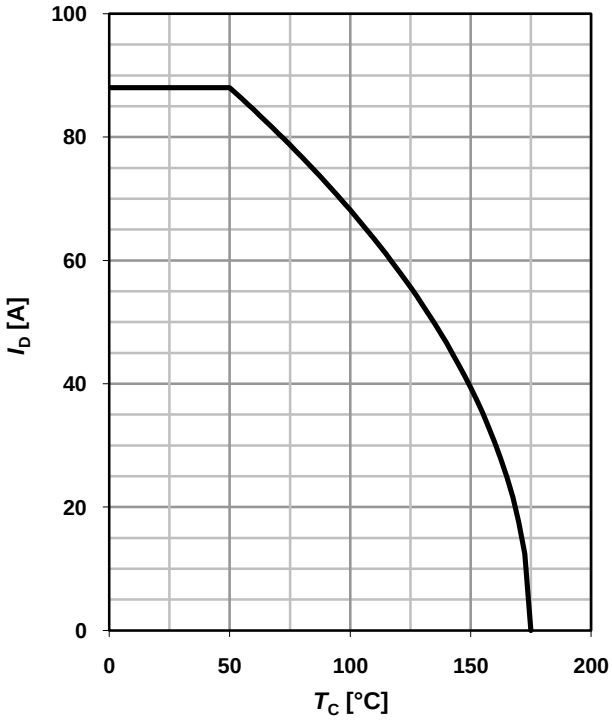
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

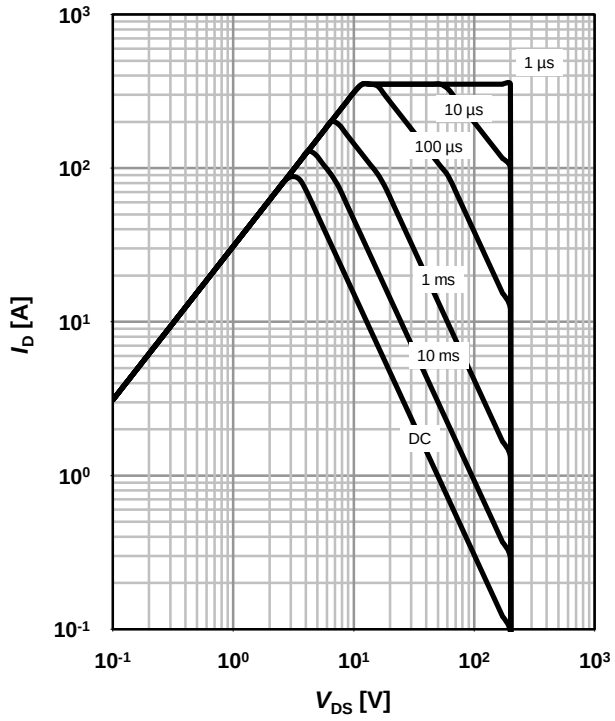
$I_D=f(T_C)$; $V_{GS}\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

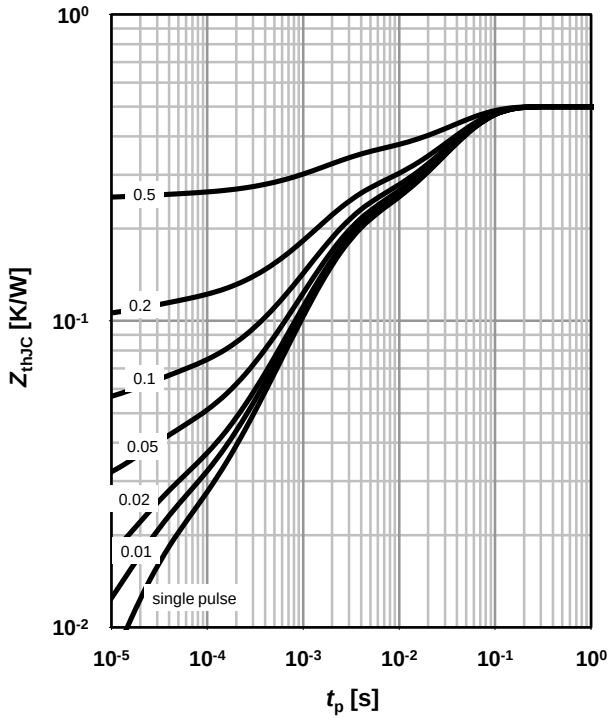
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

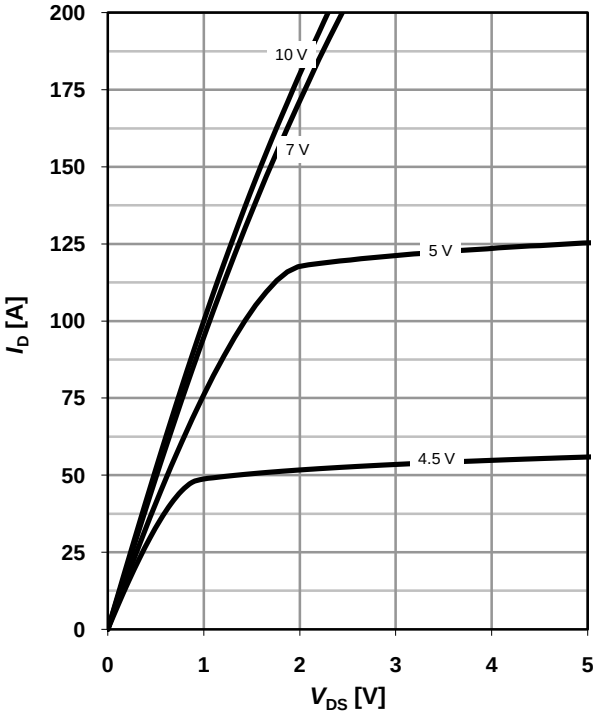
parameter: $D=t_p/T$



5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

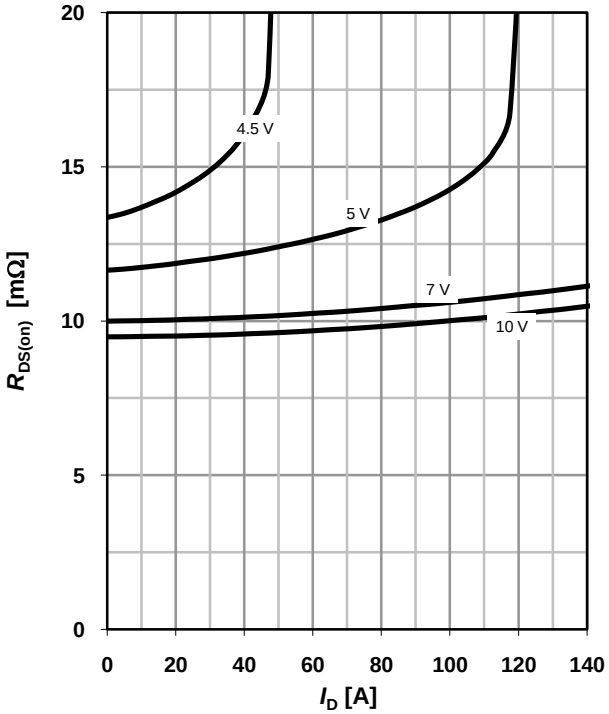
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}$=f(I_D); T_j=25 °C

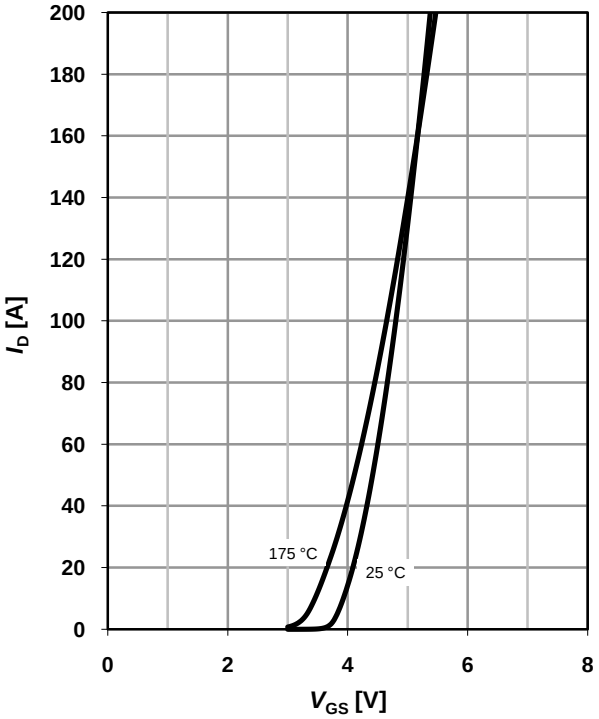
parameter: V_{GS}



7 Typ. transfer characteristics

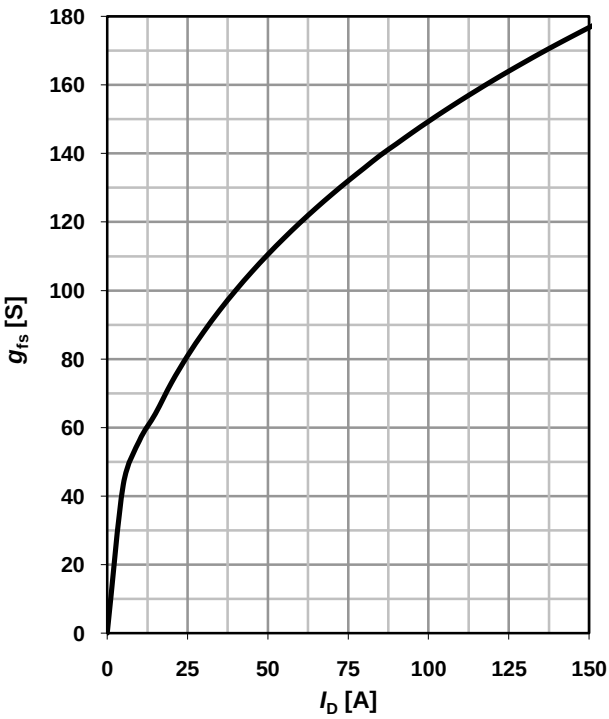
I_D=f(V_{GS}); $|V_{DS}|>2|I_D|R_{DS(on)max}$

parameter: T_j



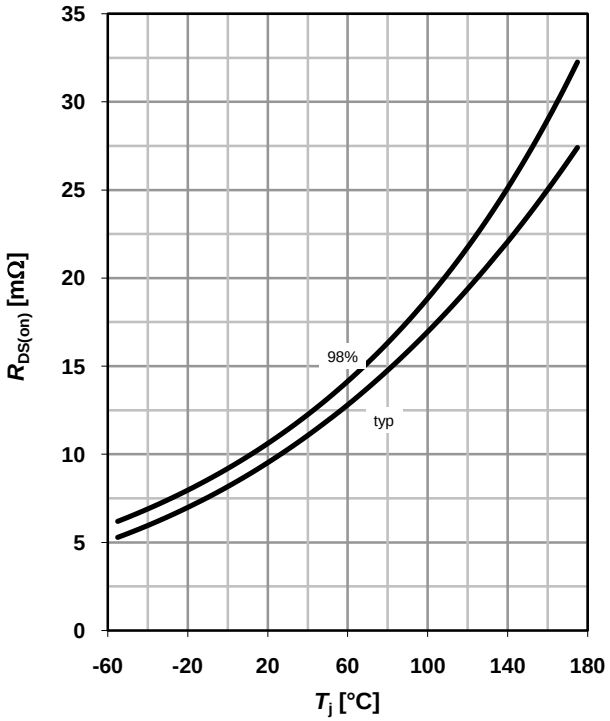
8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C



9 Drain-source on-state resistance

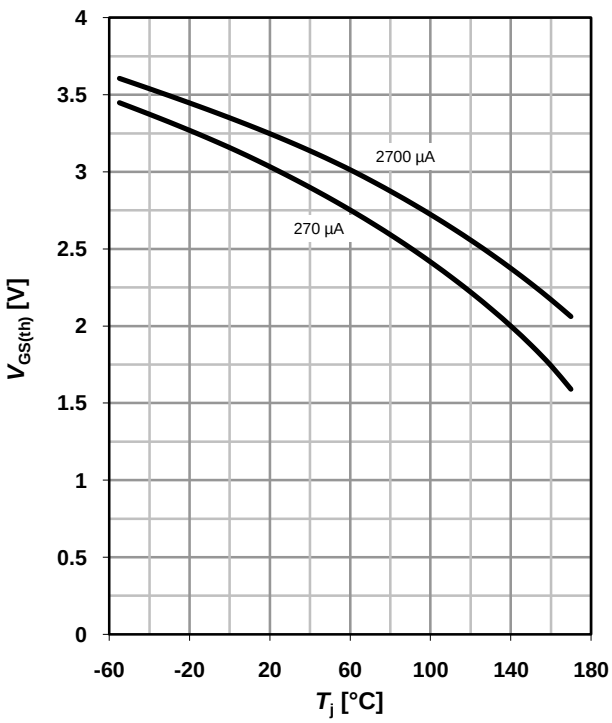
$R_{DS(on)}$=f(T_j); I_D=88 A; V_{GS}=10 V



10 Typ. gate threshold voltage

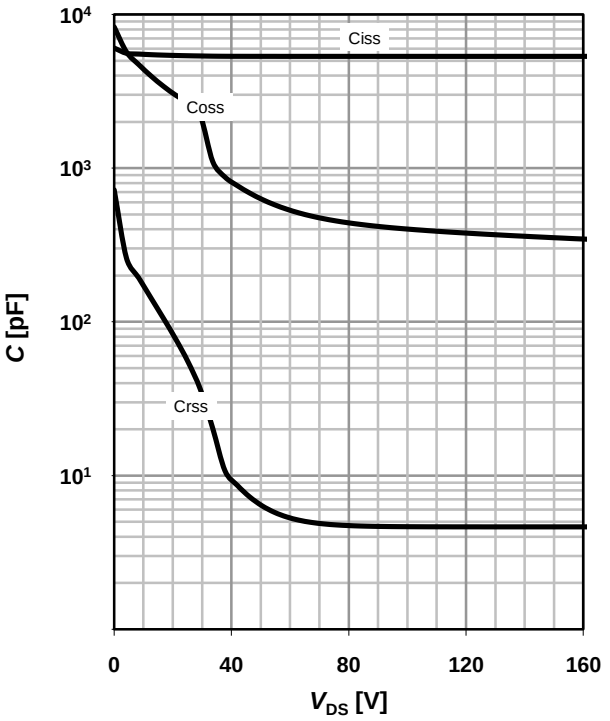
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}

parameter: I_D



11 Typ. capacitances

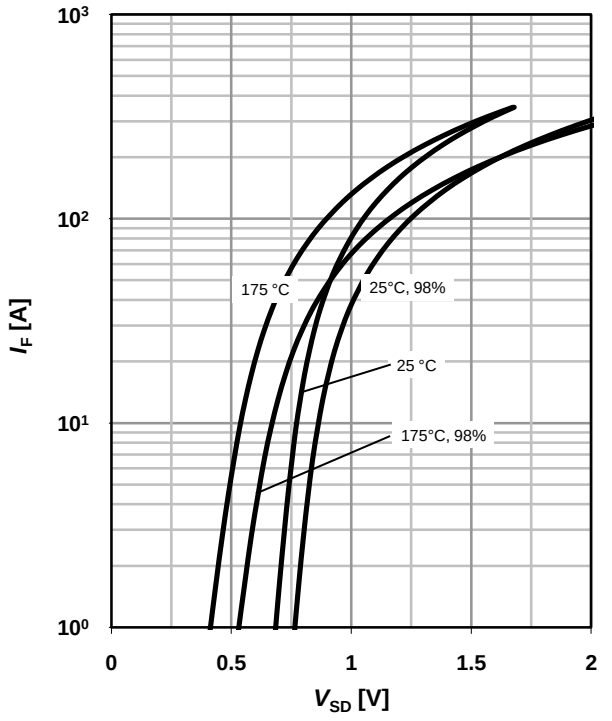
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

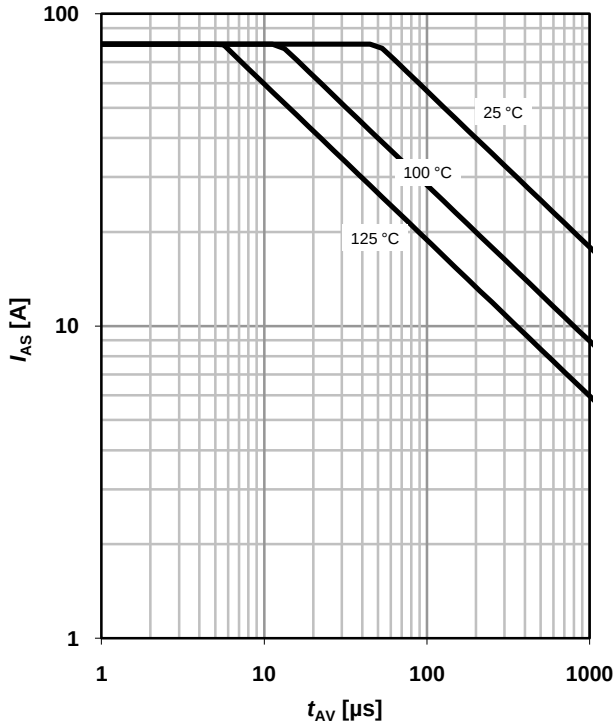
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

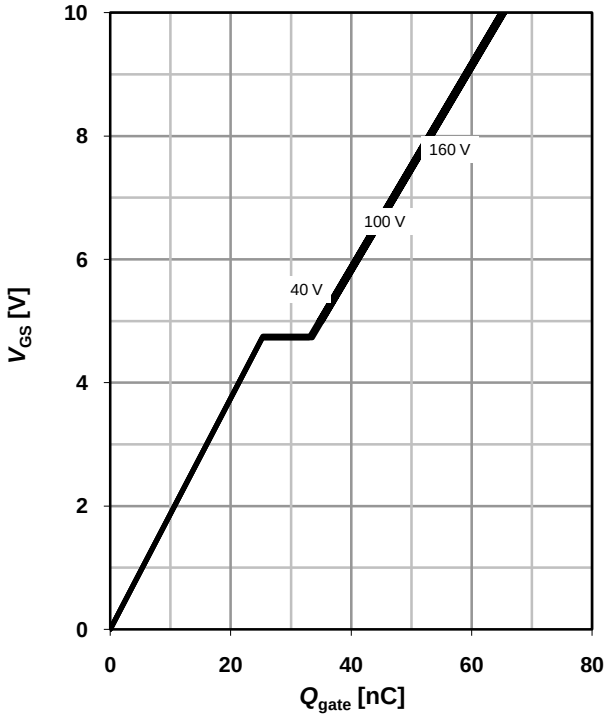
parameter: $T_{j(start)}$



14 Typ. gate charge

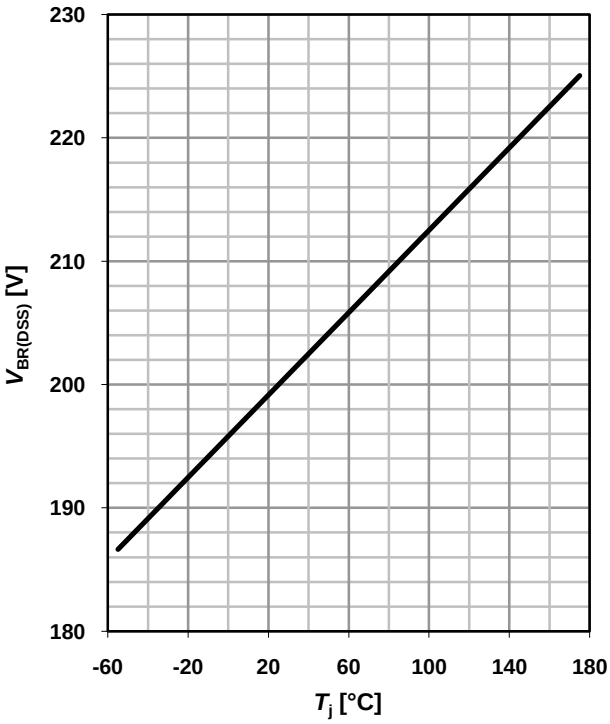
V_{GS}=f(Q_{gate}); I_D=44 A pulsed

parameter: V_{DD}

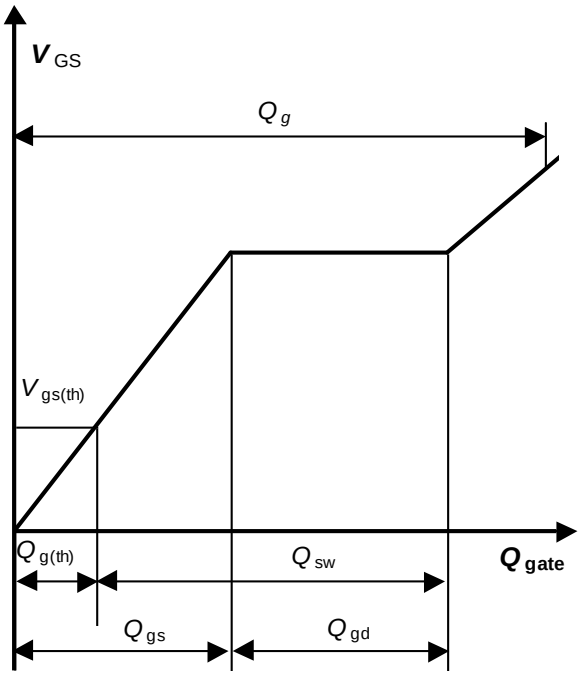


15 Drain-source breakdown voltage

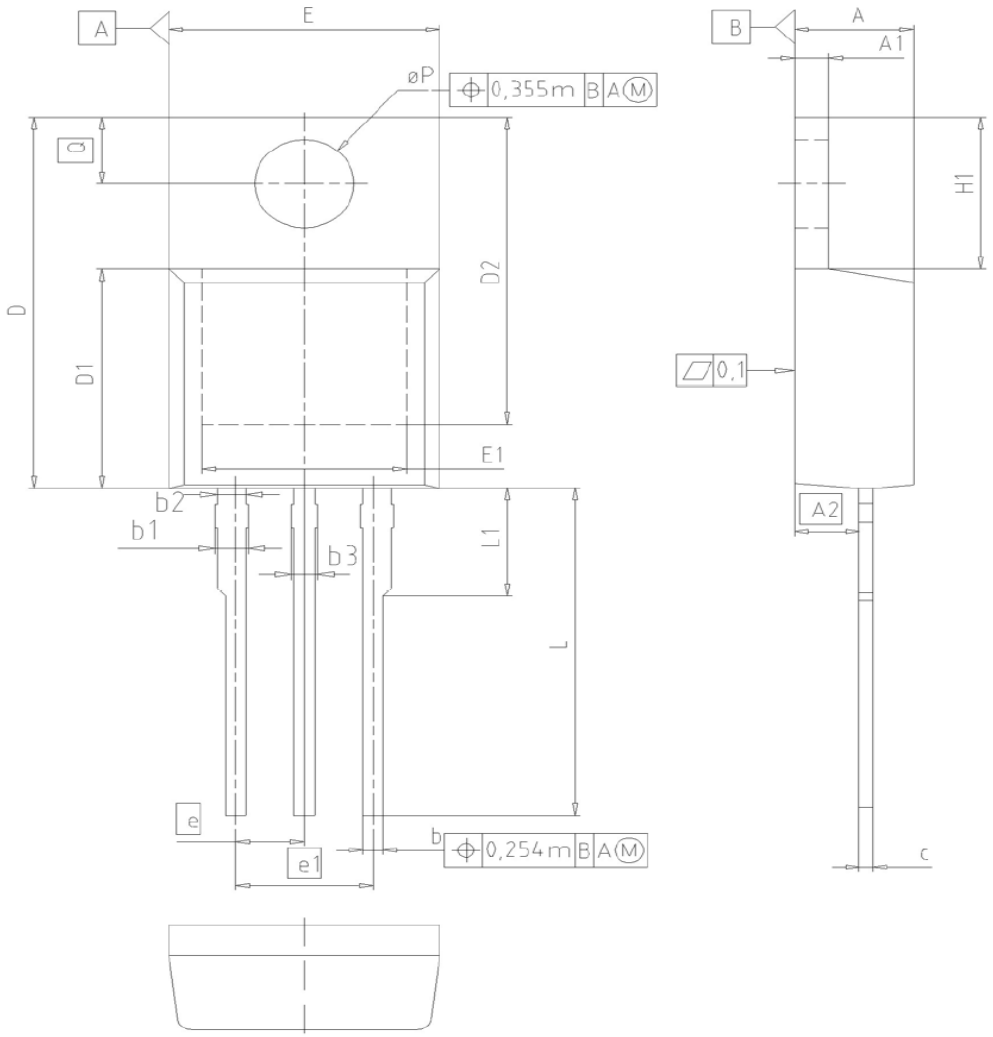
$V_{BR(DSS)}$=f(T_j); I_D=1 mA



16 Gate charge waveforms



PG-TO220-3: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00003318

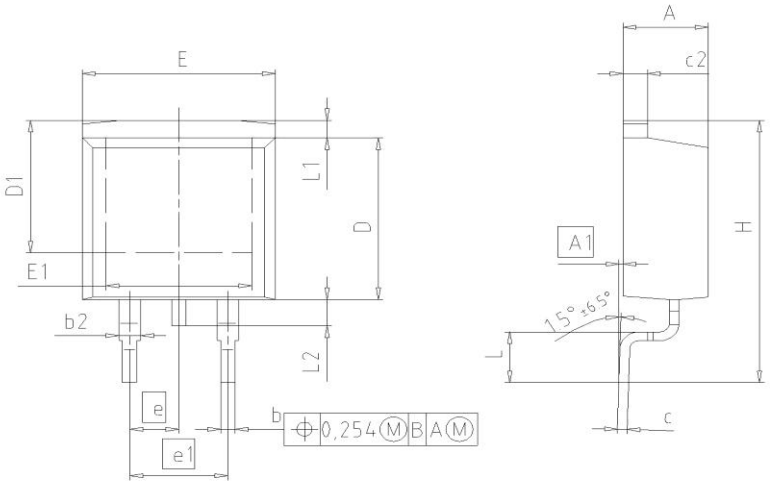
SCALE
0 2.5 5mm

EUROPEAN PROJECTION

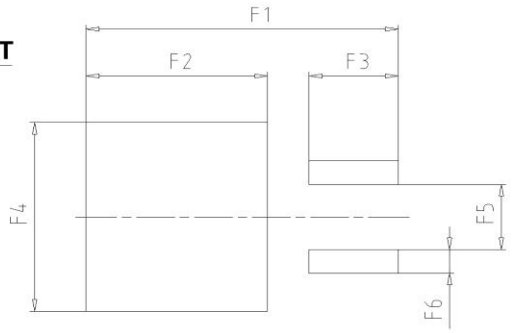
ISSUE DATE
23-08-2007

REVISION
05

PG-TO263-3: Outline



FOOTPRINT

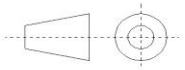


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b2	0.95	1.15	0.037	0.045
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	7.10	7.90	0.280	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

DOCUMENT NO.
Z8B00003324

SCALE
0 5 5
7.5mm

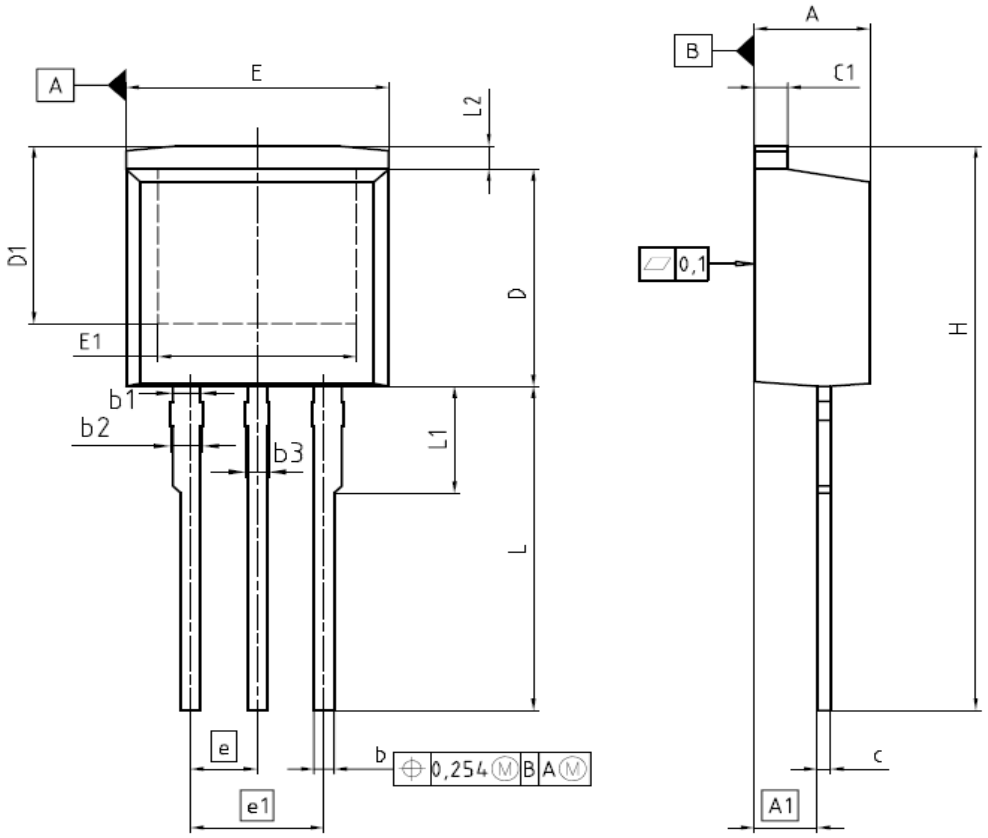
EUROPEAN PROJECTION



ISSUE DATE
30-08-2007

REVISION
01

PG-TO262-3: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	2.150	2.718	0.085	0.107
b	0.650	0.864	0.026	0.034
b1	0.950	1.093	0.037	0.043
b2	0.950	1.400	0.037	0.055
b3	0.650	1.118	0.026	0.044
c	0,330	0,600	0,013	0,024
c1	1.170	1.400	0.046	0.055
D	8,509	9,450	0,335	0,372
D1	6.900	-	0.272	-
E	9,700	10,363	0,382	0,408
E1	6,500	8,600	0,256	0,339
e	2.540		0.100	
e1	5,080		0,200	
N	3		3	
L	13,000	14,000	0,512	0,551
L1	-	4,800	-	0,189
L2	-	1,727	-	0,068

REFERENCE Z8B00003325
SCALE 0 2.5 0 2.5 5mm
EUROPEAN PROJECTION
ISSUE DATE 05-05-2006
REVISION 03

Published by
Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

on the types in question, please contact the nearest Infineon Technologies Office.
Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.